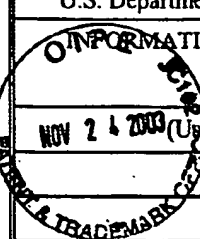


U.S. Department of Commerce, Patent and Trademark		Att'y. Docket No.	Application No.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT 		SN DK.256US0	10/052,924
		Applicant(s)	C n f. N .
		Mokhlesi	1035
		Filing Date	Group
		January 18, 2002	1035

U.S. Patent Documents

*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate

U.S. Published Patent Application Documents

*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate

Foreign Patent Documents

							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
HH	1	WO 01/27931 A1	4/19/01	PCT	—	—		
HH	2	WO 95/19047	7/13/95	PCT	—	—		

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

HH	3	Ma, "A Dual-Bit Split-Gate EPPROM (DSG) Cell in Contactless Array for Single-Vcc High Density Flash Memories," <i>Technical Digest</i> , Electron Device Meeting, 1994, pp. 3.5.1 – 3.5.4.						
HH	4	International Search Report mailed October 10, 2003.						

Examiner <u>Huan Hoang</u>	Date Considered <u>2/4/04</u>
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.	